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(54) **SUBTRACTIVE METALS AND SUBTRACTIVE METAL SEMICONDUCTOR STRUCTURES**

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(57) **ABSTRACT**

Embodiments of the present disclosure generally relate to subtractive metals, subtractive metal semiconductor structures, subtractive metal interconnects, and to processes for forming such semiconductor structures and interconnects. In an embodiment, a process for fabricating a semiconductor structure is provided. The process includes performing a degas operation on the semiconductor structure and depositing a liner layer on the semiconductor structure. The process further includes performing a sputter operation on the semiconductor structure, and depositing, by physical vapor deposition, a metal layer on the liner layer, wherein the liner layer comprises Ti, Ta, TaN, or combinations thereof, and a resistivity of the metal layer is about 30 μΩ·cm or less.